

SENSITRON **SEMICONDUCTOR**

1N5550/US
1N5551/US
1N5552/US
1N5553/US
1N5554/US

TECHNICAL DATA
DATA SHEET 126, REV F

| | |
|--------|----|
| JAN | SJ |
| JANTX | SX |
| JANTXV | SV |

HIGH CURRENT AXIAL LEAD RECTIFIERS

DESCRIPTION: 200-1000 VOLT, 3.0 AMP, 2000 NANOSECOND RECTIFIER

-Suffix "US" denotes melf/surface mount packaging

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^\circ\text{C}$ unless otherwise specified.

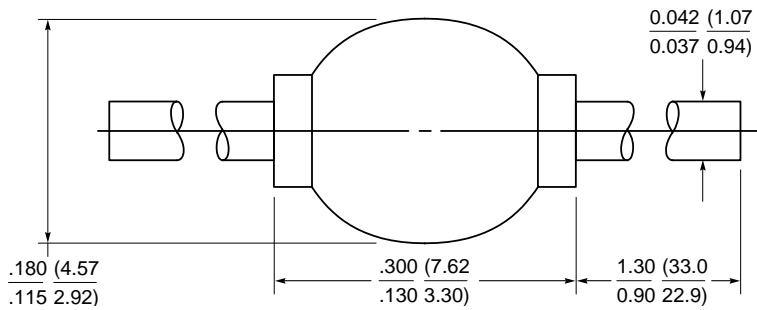
| RATING | CONDITIONS | MIN | TYP | MAX | UNIT |
|---|--|-----|-----|----------------------------------|--------------------|
| Peak Inverse Voltage (PIV) 1N5550 1N5551 1N5552 1N5553 1N5554 | - | - | - | 200 400 600 800 1000 | Vdc |
| Average DC Output Current (I_o) | $T_A = +55^\circ\text{C}$ | - | - | 3.0 | Amps |
| Peak Single Cycle Surge Current (I_{fsm}) | $t_p = 8.3$ ms Single Half Cycle Sine Wave, Superimposed On Rated Load | - | - | 150 | Amps(pk) |
| Operating and Storage Temp. (T_{op} & T_{stg}) | - | -65 | - | +175 | $^\circ\text{C}$ |
| Maximum Forward Voltage (V_f) 1N5550 1N5551 1N5552 1N5553 1N5554 | $I_f = 9.0\text{A}$ (300 μsec pulse, duty cycle < 2%) | - | - | 1.2 1.2 1.2 1.3 1.3 | Volts |
| Maximum Instantaneous Reverse Current At Rated (PIV) | $T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$ | - | - | 1.0 75 | μAmps |
| Reverse Recovery Time (t_{rr}) | $I_f = 0.5\text{A}$, $I_r = 1.0\text{A}$, $I_{rr} = 0.25\text{A}$ | - | - | 2000 | nsec |
| Thermal Resistance (θ_{JL}) | Junction to Lead $d = 0.375''$ | - | - | 22 | $^\circ\text{C/W}$ |
| Thermal Resistance (θ_{JEC}) | Junction to Endcap | - | - | 11 | $^\circ\text{C/W}$ |

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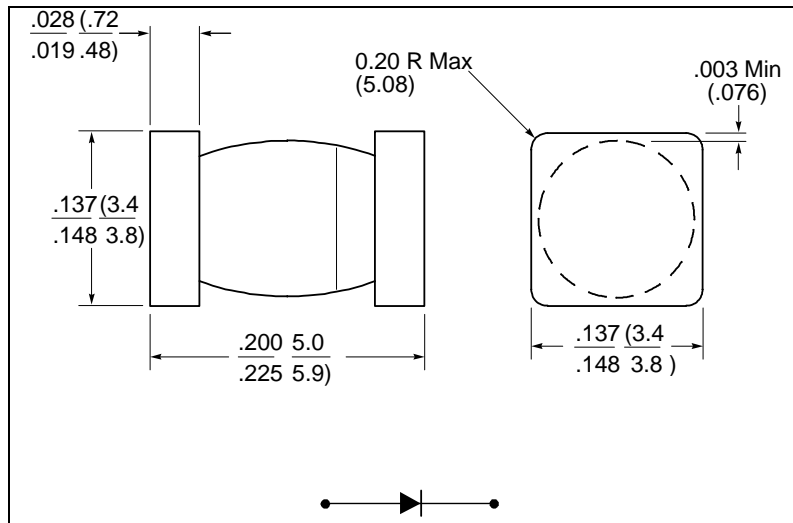
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DATA SHEET 126, REV F

MECHANICAL DIMENSIONS In Inches / (mm), min./max.



PKG. 301

Note: The cathode side is marked with a dark colored band on one side of the diode body.



MELF-B

Note: The cathode side is marked on body with a dark band.

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